L Number	Hits	Search Text	DB	Time stamp
_	4	'gate oxide' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO;	2003/08/22 07:29
-	7	@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/08/22
-	1	@ad<=20020219 and 'ONO' and 'ISSG'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 08:28
_	10	<pre>@ad<=20020219 and 'in-situ steam generation' or 'ISSG'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/24 08:32
-	52	(438/954).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:24
-	245	(438/593).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	627	(438/770).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	481	(438/264).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	208	(438/594).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:27
-	518	(438/275).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	323	(438/199).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	91	(438/477).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:28
-	77	(438/216).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	577	(438/287).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:29
			DERWENT; IBM TDB	

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-	166	(438/783).ccls. and @ad<=20020119	USPAT;	2002/05/24
			US-PGPUB; EPO; JPO;	13:29
			DERWENT; IBM TDB	
-	8	'gate oxide' and 'in-situ steam generation' or 'LP-RTP'	USPĀT; US-PGPUB;	2002/10/16 10:36
		generation of LP-RIP	EPO; JPO;	10:36
			DERWENT; IBM TDB	
-	2	("5324675").PN.	USPAT;	2002/10/16
			US-PGPUB; EPO; JPO;	10:11
			DERWENT; IBM TDB	
-	1		USPĀT;	2002/10/16
		and 'in-situ steam generation' or 'LP-RTP'	US-PGPUB; EPO; JPO;	10:49
			DERWENT; IBM TDB	
-	27216	@ad<=20020219 and 'TFT'	USPĀT;	2002/10/16
			US-PGPUB; EPO; JPO;	10:35
			DERWENT; IBM TDB	,
-	0	(USPĀT;	2002/10/16
		'ISSG'	US-PGPUB; EPO; JPO;	10:38
			DERWENT; IBM TDB	
-	0	(USPĀT;	2002/10/16
		'in-situ steam generation'	US-PGPUB; EPO; JPO;	10:38
			DERWENT; IBM TDB	
-	0	1 (000 - 20020220 0000 202 / 00000 000200 00000	USPĀT;	2002/10/16
		'LP-RTP'	US-PGPUB; EPO; JPO;	10:39
			DERWENT; IBM TDB	
-	226	(@ad<=20020219 and 'TFT') and 'floating gate'	USPAT; US-PGPUB;	2002/10/16 10:39
		gate	EPO; JPO;	10:39
			DERWENT; IBM TDB	
-	169	(@ad<=20020219 and 'TFT') and 'oxide' and 'floating gate'	USPĀT; US-PGPUB;	2002/10/16 10:55
			EPO; JPO;	10.00
			DERWENT; IBM_TDB	
-	1	'tft' and 'in-situ steam generation' or 'LP-RTP'	USPAT; US-PGPUB;	2002/10/16 11:12
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	0	'tft' and 'in-situ steam generation'	USPĀT; US-PGPUB;	2002/10/16 10:51
			EPO; JPO;	
			DERWENT; IBM_TDB	
_	64	(@ad<=20020219 and 'TFT') and 'oxide layer' and 'floating gate'	USPAT; US-PGPUB;	2002/10/16 11:04
			EPO; JPO; DERWENT;	
			IBM_TDB	0000/10/55
_	571	(438/149).CCLS.	USPAT; US-PGPUB;	2002/10/16 11:05
			EPO; JPO; DERWENT;	
	<u> </u>		IBM TDB	

	1 4 4	0-1-20000014 - 1 (400 (140)	1	1 0 0 0 0 1 0 1 0 0
-	11	@ad<=20020214 and (438/149).ccls. and 'floating gate'	USPAT;	2002/10/16
1		IIOacIMy gate	US-PGPUB; EPO; JPO;	11:06
			DERWENT;	
			IBM_TDB	
-	3585	((438/294) or (438/954) or (438/593-594)	USPAT;	2002/10/17
		or (438/770) or (438/264) or (438/275) or		09:50
		(438/199) or (438/477) or (438/216) or (438/287) or (438/783)).CCLS.	EPO; JPO;	
		(436/267) OF (436/763)).CCLS.	DERWENT; IBM TDB	
_	15	@ad<=20020219 and 'ISSG'	USPAT;	2003/02/26
			US-PGPUB;	11:57
			EPO; JPO;	
			DERWENT;	
_] 30	00dx-20020210 and 10V01 and 14- aits	IBM_TDB	2002/00/06
-	29	<pre>@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'</pre>	USPAT; US-PGPUB;	2003/02/26
		Steam generation of 1556	EPO; JPO;	12.54
			DERWENT;	
			IBM_TDB	
-	27	@ad<=20020219 and 'ISSG'	USPĀT;	2003/02/26
			US-PGPUB;	12:07
			EPO; JPO;	
]		DERWENT; IBM TDB	
_	2	@ad<=20020219 and 'low pressure rapid	USPAT;	2003/02/26
	[thermal process'	US-PGPUB;	12:17
			EPO; JPO;	,
			DERWENT;	·
_	416	@ad<=20020219 and 'TFT' and 'ONO'	IBM_TDB	2002/02/23
_	410	ead-20020219 and Trr and ONO.	USPAT; US-PGPUB;	2003/02/27 07:12
			EPO; JPO;	07.12
			DERWENT;	
			IBM_TDB	
_	0	@ad<=20020219 and 'TFT' and 'ONO' and	USPAT;	2003/02/27
		'ISSG'	US-PGPUB;	07:12
1			EPO; JPO; DERWENT;	
			IBM TDB	
-	0	@ad<=20020219 and 'TFT' and 'ISSG'	USPĀT;	2003/02/27
			US-PGPUB;	07:13
			EPO; JPO;	
			DERWENT; IBM TDB	
-	71	@ad<=20020219 and 'in-situ steam	USPAT;	2003/08/22
	'-	generation' or 'ISSG'	US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
_	2	/"6525394"\ DN	IBM_TDB	2002/09/22
-		("6525384").PN.	USPAT; US-PGPUB;	2003/08/22
			EPO; JPO;	02.30
			DERWENT;	
			IBM_TDB	
-	2	"20030155582"	USPAT;	2004/02/23
]			US-PGPUB;	09:45
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2	'TFT' and 'in-situ steam generation'	USPAT;	2004/02/23
		-	US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
_	2	("5700699").PN.	<pre>IBM_TDB USPAT;</pre>	2004/02/23
		(2.300)	US-PGPUB;	09:59
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

	0	Ithin film transistant many ligari	USPAT;	2004/02/23
-		'thin film transistor' near 'issg'		10:04
			US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
 -	0	'tft' near 'issg'	USPAT;	2004/02/23
			US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	0	'TFT' near 'in-situ steam generation'	USPAT;	2004/02/23
			US-PGPUB;	10:30
			EPO; JPO;	
			DERWENT;	
Ì			IBM TDB	
_	0	'TFT' near 'free radical enhanced rapid	USPAT;	2004/02/23
		thermal oxidation'	US-PGPUB;	10:31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	i i
_	0	'TFT' same 'free radical enhanced rapid	USPAT;	2004/02/23
		thermal oxidation'	US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
	'		IBM TDB	
_	1	'TFT' and 'free radical enhanced rapid	USPAT;	2004/02/23
1	*	thermal oxidation'	US-PGPUB;	10:32
		Circinal Oniadolon	EPO; JPO;	
			DERWENT;	
			IBM TDB	
I	1		TON TUB	